L Number	Hits		DB	Time stamp
-	155637		USPAT;	2004/08/10 13:43
		polycrystal\$5) adj (si or silicon)	US-PGPUB;	
			EPO; JPO;	
			DERWENT;	
_	656558	stress\$4	USPAT;	2004/08/10 09:04
:	030330	30163374	US-PGPUB;	2004/08/10 09:04
'			EPO; JPO;	
			DERWENT;	
			IBM TDB	
-	3947590	anneal\$4 or heat\$4 or thermal\$3 adj3	USPAT;	2004/08/10 13:48
		treat\$5	US-PGPUB;	
			EPO; JPO;	
			DERWENT;	
	070076		IBM_TDB	0004/00/10 10:45
_	878976	gate	USPAT;	2004/08/10 13:45
			US-PGPUB; EPO; JPO;	
			DERWENT;	
			IBM TDB	
_	718828	oxidi\$5 or oxidat\$5	USPAT;	2004/08/10 11:33
			US-PGPUB;	
			EPO; JPO;	
			DERWENT;	
			IBM_TDB	
-	30152		USPĀT;	2004/08/10 09:10
		polysilicon or (poly or polycrystal\$5) adj	US-PGPUB;	
		(si or silicon))	EPO; JPO;	
			DERWENT;	
	111000		IBM_TDB	0004/00/10 00 10
_	114339		USPAT;	2004/08/10 09:10
		thermal\$3 adj3 treat\$5)	US-PGPUB; EPO; JPO;	
			DERWENT;	
			IBM TDB	
_	956	((oxidi\$5 or oxidat\$5) same (polysi or	USPAT;	2004/08/10 09:12
) 550	polysilicon or (poly or polycrystal\$5) adj	US-PGPUB;	2001,00,20
		(si or silicon))) and (stress\$4 same	EPO; JPO;	
		(anneal\$4 or heat\$4 or thermal\$3 adj3	DERWENT;	
		treat\$5)) and gate	IBM_TDB	
-	2478932	tungsten or w	USPAT;	2004/08/10 13:57
			US-PGPUB;	
			EPO; JPO;	
			DERWENT;	
	643	///	IBM_TDB	2004/08/10 08-24
_	643	(((oxidi\$5 or oxidat\$5) same (polysi or polysilicon or (poly or polycrystal\$5) adj	USPAT; US-PGPUB;	2004/08/10 09:24
	•	(si or silicon))) and (stress\$4 same	EPO; JPO;	
		(anneal\$4 or heat\$4 or thermal\$3 adj3	DERWENT;	
		treat\$5)) and gate) and (tungsten or w)	IBM TDB	
_	19778	gate with stack\$4	USPAT;	2004/08/10 09:26
			US-PGPUB;	
			EPO; JPO;	
			DERWENT;	
			IBM_TDB	
-	182	` '	USPAT;	2004/08/10 11:32
		polysilicon or (poly or polycrystal\$5) adj	US-PGPUB;	
		(si or silicon))) and (stress\$4 same	EPO; JPO;	
		(anneal\$4 or heat\$4 or thermal\$3 adj3	DERWENT; IBM TDB	
_	2513	treat\$5)) and (gate with stack\$4) 438/585.ccls. or 438/592.ccls. or	USPAT;	2004/08/10 10:06
•	2313	438/595.ccls. or 438/592.ccls. or 438/595.ccls.	US-PGPUB;	2007/00/10 10.00
		100/000.0013.	EPO; JPO;	
			DERWENT;	
	ļ		IBM TDB	
_	546619	defect or trap	USPAT;	2004/08/10 11:32
		_	US-PGPUB;	
			EPO; JPO;	
			DERWENT;	
	I	1	IBM TDB	Ī

_	6508889	suppress\$4 or reduc\$4 or decreas\$4	USPAT; US-PGPUB;	2004/08/10 11:34
			EPO; JPO;	
			DERWENT;	
_	720568	oxidi\$5 or oxidat\$5 or reoxidi\$5 or	IBM_TDB USPAT;	2004/08/10 13:43
	720300	reoxidat\$5	US-PGPUB;	2004/00/10 13.43
			EPO; JPO;	
			DERWENT;	
	7250101	, , , , , , , , , , , , , , , , , , , ,	IBM_TDB	0004/00/10 12 04
_	7352191	suppress\$4 or reduc\$4 or decreas\$4 or releas\$5	USPAT; US-PGPUB;	2004/08/10 11:34
		16164373	EPO; JPO;	
			DERWENT;	,
			IBM_TDB	
-	50316		USPAT;	2004/08/10 11:37
		treat\$5) same (suppress\$4 or reduc\$4 or decreas\$4 or releas\$5) same (oxidi\$5 or	US-PGPUB; EPO; JPO;	
		oxidat\$5 or reoxidi\$5 or reoxidat\$5)	DERWENT;	
			IBM TDB	
_	30328	(oxidi\$5 or oxidat\$5 or reoxidi\$5 or	USPĀT;	2004/08/10 11:37
		reoxidat\$5) same (polysi or polysilicon or	US-PGPUB;	
		(poly or polycrystal\$5) adj (si or silicon))	EPO; JPO; DERWENT;	
		SIIICON,	IBM TDB	
-	1857	((anneal\$4 or heat\$4 or thermal\$3 adj3	USPAT;	2004/08/10 11:37
		treat\$5) same (suppress\$4 or reduc\$4 or	US-PGPUB;	
		decreas\$4 or releas\$5) same (oxidi\$5 or oxidat\$5 or reoxidi\$5 or reoxidat\$5)) and	EPO; JPO;	
		((oxidi\$5 or oxidat\$5 or reoxidi\$5 or	DERWENT; IBM TDB	
		reoxidat\$5) same (polysi or polysilicon or	15155	
		(poly or polycrystal\$5) adj (si or		,
	700560	silicon))) and gate		0004/00/10 14 51
-	720568	oxidi\$5 or oxidat\$5 or reoxidi\$5 or reoxidat\$5	USPAT; US-PGPUB;	2004/08/10 14:51
		leonidaeys	EPO; JPO;	
			DERWENT;	
			IBM_TDB	0004/00/10 10 15
_	155637	polysi or polysilicon or (poly or polycrystal\$5) adj (si or silicon)	USPAT; US-PGPUB;	2004/08/10 13:45
		polyclystalv3) adj (si ol silicon)	EPO; JPO;	
			DERWENT;	
			IBM_TDB	
-	878976	gate	USPAT;	2004/08/10 13:46
			US-PGPUB; EPO; JPO;	
			DERWENT;	
			IBM_TDB	
_	1523136		USPAT;	2004/08/10 13:47
		"sio.sub2."	US-PGPUB; EPO; JPO;	
			DERWENT;	
	1		IBM_TDB	
-	2738813	sidewall or side adj2 wall or edge	USPAT;	2004/08/10 13:48
			US-PGPUB; EPO; JPO;	
			DERWENT;	
			IBM_TDB	
-	3947590	anneal\$4 or heat\$4 or thermal\$3 adj3	USPAT;	2004/08/10 13:49
		treat\$5	US-PGPUB; EPO; JPO;	
			DERWENT;	
			IBM_TDB	
-	30115	(oxidi\$5 or oxidat\$5 or reoxidi\$5 or	USPAT;	2004/08/10 13:51
		reoxidat\$5) near10 ((polysi or polysilicon or (poly or polycrystal\$5) adj	US-PGPUB; EPO; JPO;	
		(si or silicon)) or gate)	DERWENT;	
		, , 5 ,	IBM_TDB	

_	35576	(oxide or dioxide or "sio.sub.2" or "sio.sub2.") near10 (sidewall or side adj2 wall or edge)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2004/08/10 13:53
-	9036	<pre>((oxidi\$5 or oxidat\$5 or reoxidi\$5 or reoxidat\$5) near10 ((polysi or polysilicon or (poly or polycrystal\$5) adj (si or silicon)) or gate)) and ((oxide or dioxide or "sio.sub.2" or "sio.sub2.") near10 (sidewall or side adj2 wall or edge))</pre>	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/08/10 13:54
-	3276		USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/08/10 13:56
_	512		USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/08/10 13:56
_	2478932	tungsten or w	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/08/10 13:57
	11519	<pre>(polysi or polysilicon or (poly or polycrystal\$5) adj (si or silicon)) same gate same (tungsten or w)</pre>	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2004/08/10 13:58
-	141	<pre>((((oxidi\$5 or oxidat\$5 or reoxidi\$5 or reoxidat\$5) near10 ((polysi or polysilicon or (poly or polycrystal\$5) adj (si or silicon)) or gate)) same ((oxide or dioxide or "sio.sub.2" or "sio.sub2.") near10 (sidewall or side adj2 wall or edge))) same (anneal\$4 or heat\$4 or thermal\$3 adj3 treat\$5)) and ((polysi or polysilicon or (poly or polycrystal\$5) adj (si or silicon)) same gate same (tungsten or w))</pre>	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/08/10 14:50
	141	(((((oxidi\$5 or oxidat\$5 or reoxidi\$5 or reoxidat\$5) near10 ((polysi or polysilicon or (poly or polycrystal\$5) adj (si or silicon)) or gate)) same ((oxide or dioxide or "sio.sub.2" or "sio.sub2.") near10 (sidewall or side adj2 wall or edge))) same (anneal\$4 or heat\$4 or thermal\$3 adj3 treat\$5)) and ((polysi or polysilicon or (poly or polycrystal\$5) adj (si or silicon)) same gate same (tungsten or w))) and (anneal\$4 or heat\$4 or thermal\$3 adj3 treat\$5)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/08/10 14:21
	8935	selectivi\$4 near3 (oxidi\$5 or oxidat\$5) or reoxidi\$5 or reoxidat\$5	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2004/08/10 14:53
_	635	<pre>(selectivi\$4 near3 (oxidi\$5 or oxidat\$5) or reoxidi\$5 or reoxidat\$5) near15 ((polysi or polysilicon or (poly or polycrystal\$5) adj (si or silicon)) or gate)</pre>	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2004/08/10 14:55

	19977	(oxide or dioxide or "sio.sub.2" or	USPAT;	1 2004 /00 /10 14-50
_	19977	"sio.sub2.") near20 ((sidewall or side	US-PGPUB;	2004/08/10 14:59
		adj2 wall or edge) or side adj2 surface)	EPO; JPO;	
		near20 ((polysi or polysilicon or (poly or	DERWENT;	
		polycrystal\$5) adj (si or silicon)) or	IBM TDB	
		1	TDM_TDD	
l _	116	gate)	USPAT:	2004/08/10 14:59
-	110	((selectivi\$4 near3 (oxidi\$5 or oxidat\$5) or reoxidi\$5 or reoxidat\$5) near15	US-PGPUB;	2004/08/10 14:59
		((polysi or polysilicon or (poly or	EPO; JPO;	
		polycrystal\$5) adj (si or silicon)) or	DERWENT;	
		gate)) same ((oxide or dioxide or	IBM_TDB	
		"sio.sub.2" or "sio.sub2.") near20		
	Ì	((sidewall or side adj2 wall or edge) or		
		side adj2 surface) near20 ((polysi or		
		polysilicon or (poly or polycrystal\$5) adj		
	70	(si or silicon)) or gate))	HODAM.	2004/00/10 15:40
-	78	(((000000000000000000000000000000000000	USPAT;	2004/08/10 15:48
		or reoxidi\$5 or reoxidat\$5) near15	US-PGPUB;	
		((polysi or polysilicon or (poly or	EPO; JPO;	
		polycrystal\$5) adj (si or silicon)) or	DERWENT;	
		gate)) same ((oxide or dioxide or	IBM_TDB	
		"sio.sub.2" or "sio.sub2.") near20		
		((sidewall or side adj2 wall or edge) or		
		side adj2 surface) near20 ((polysi or		ļ
		polysilicon or (poly or polycrystal\$5) adj		
		(si or silicon)) or gate))) and		
		(anneal\$4 or heat\$4 or thermal\$3 adj3		
	1105	treat\$5)	II G D A M	2004/00/10 15 40
-	1105	438/592.ccls.	USPAT;	2004/08/10 15:49
			US-PGPUB;	
			EPO; JPO;	
			DERWENT;	
			IBM TDB	